

6501130 NATL SEMICOND, (DISCRETE)

28C 35460 D

T-33-01

NP Transistors

2



POWER

Type No.	Case Style	V _{CB0} (V) Min	V _{CE0} (V) Min	V _{EB0} (V) Min	I _{CEX} [†] (μA) Max	V _{CB} (V) Min	I _{CE} (A) Max	V _{CE} (V) Min	V _{CE(SAT)} (V) Max	V _{BE(SAT)} (V) Min	I _C (A) Max	C _{ob} (pF) Max	f _T (MHz) Min	I _C (A) Max	Process No.
MJE170	TO-126		40		0.1	60	1.5	1	1.7	2.0	3	50	50	0.1	77
MJE710	TO-126		40		100 [†]	40	0.5	1	0.9	1.5	1.5				77
MJE171	TO-126		60		0.1	80	1	1	1.0	1.3	0.5				78
MJE711	TO-126		60		100 [†]	80	0.5	1	0.4		0.5				78
MJE172	TO-126		80		0.1	100	1.5	1	1.7	2.0	3	50	50	0.1	79
MJE712	TO-126		80		100 [†]	80	0.5	1	0.9	1.5	0.5				79
2N6489	TO-220		40		500 [†]	45	15	4	1.3		5		5	1	5A
2N6490	TO-220		60		500 [†]	65	15	4	1.3		5		5	1	5A
2N6491	TO-220		80		500 [†]	85	15	4	1.3		5		5	1	5A
MJE2901T	TO-220		60				100	3	3.5		15				5A
MJE2955T	TO-220		60		1 mA	70	4	4	1.1		4				5A
TIP42	TO-220		40		400*	40	3	4	1.5		6		3	0.5	5A
TIP42A	TO-220		60		400*	60	3	4	1.5		6		3	0.5	5A
TIP42B	TO-220		80		400*	80	3	4	1.5		6		3	0.5	5A
TIP42C	TO-220		100		400*	100	3	4	1.5		6		3	0.5	5A

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POWER (Continued)



Type No.	Case Style	V _{CE0} (V) Min	V _{CE0} (V) Min	V _{BE0} (V) Min	I _{CE0} [†] (μA) Max	V _{CB} (V) Min	I _{CE0} [†] (μA) Max	I _{CE0} [†] (μA) Max	V _{CE(SAT)} (V) Max	V _{BE(SAT)} (V) Max	I _C (A) Max	C _{ob} (pF) Max	f _T (MHz) Min	I _C (A) Max	Process No.
2N5193	TO-126	40	40	40	100	40	100	100	0.6	1.5	1		2	1	5E
2N5194	TO-126	60	60	60	100	60	100	100	0.6	1.5	1		2	1	5E
2N5195	TO-126	80	80	80	100	80	100	100	0.6	1.5	1		2	1	5E
2N6107	TO-220	70	70	70	100	75	100	100	1.0	2.0	0.5	250	10	0.5	5E
2N6109	TO-220	50	50	50	100	56	100	100	1.0	2.5	0.5	250	10	0.5	5E
2N6110	TO-220 Lead Form + Clip	30	30	30	100	37.5	100	100	1.0	2.0	0.5	250	10	0.5	5E
2N6111	TO-220	30	30	30	100	37.5	100	100	1.0	2.0	0.5	250	10	0.5	5E
2N6124	TO-220	45	45	45	100	45	100	100	0.6	1.5	1		2.5	1	5E
2N6125	TO-220	60	60	60	100	60	100	100	0.6	1.5	1		2.5	1	5E
2N6126	TO-220	80	80	80	100	80	100	100	0.6	1.5	1		2.5	1	5E
2N6132	TO-220	40	40	40	100	40	100	100	1.4	7	1		2.5	1	5E
2N6133	TO-220	60	60	60	100	60	100	100	1.4	7	1		2.5	1	5E
2N6134	TO-220	80	80	80	100	80	100	100	2.0	7	1		2.5	1	5E
MJE371	TO-220	40	40	40	100	40	100	100	0.6	1.3	0.25	100	3	0.25	5F
2N4918	TO-126	40	40	40	100	40	100	100	0.6	1.3	0.25	100	3	0.25	5F
2N4919	TO-126	60	60	60	100	60	100	100	0.6	1.3	0.25	100	3	0.25	5F
2N4920	TO-126	80	80	80	100	80	100	100	0.6	1.3	0.25	100	3	0.25	5F

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POWER (Continued)



Type No.	Case Style	V _{CEO} (V) Min	V _{CE0} (V) Min	V _{EB0} (V) Min	I _{CEX} [†] (μA) Max	V _{CB} (V) @ I _C	h _{FE} Min	I _C (A) @ V _{CE} & V _{BE(SAT)} Max	V _{CE(SAT)} (V) Max	V _{BE(SAT)} (V) Min	I _C (A) @ V _{CE(SAT)} & V _{BE(SAT)} Max	C _{ob} (pF) Max	f _T (MHz) Min	I _C (A) @ f _T Max	Process No.
2N6475	TO-220		100		100	100	15	1.5	1.2		1.5	250	10	0.5	5F
2N6476	TO-220		120		100	120	15	1.5	1.2		1.5	250	10	0.5	5F
MJE370	TO-220		30				25	0.2							5F
TIP30	TO-220		40		200*	40	15	0.2	0.7		1		3	0.2	5F
TIP30A	TO-220		60		200*	60	15	0.2	0.7		1		3	0.2	5F
TIP30B	TO-220		80		200*	80	15	0.2	0.7		1		3	0.2	5F
TIP30C	TO-220		100		200*	100	15	0.2	0.7		1		3	0.2	5F
TIP32	TO-220		40		200*	40	10	0.2	1.2		3		3	0.5	5F
TIP32A	TO-220		60		200*	60	10	0.2	1.2		3		3	0.5	5F
TIP32B	TO-220		80		200*	80	10	0.2	1.2		3		3	0.5	5F
TIP32C	TO-220		100		200*	100	10	0.2	1.2		3		3	0.5	5F
TIP62	TO-220		40		200*	40	15	0.5	0.7		0.5		3	0.05	5F
TIP62A	TO-220		60		200*	60	15	0.5	0.7		0.5		3	0.05	5F
TIP62B	TO-220		80		200*	80	15	0.5	0.7		0.5		3	0.05	5F
TIP62C	TO-220		100		200*	100	15	0.5	0.7		0.5		3	0.05	5F
D43C1	TO-202 (56)		30		1 μA	1	10	1A	0.5		1.3	30			5P
D43C2	TO-202 (56)		30		1 μA	30	20	1A	0.5		1.3	30			5P
D43C3	TO-202 (56)		30		1 μA	30	20	1A	0.5		1.3	30			5P

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POWER (Continued)

Type No.	Case Style	V _{CB} (V) Min	V _{CEO} (V) Min	V _{EB} (V) Min	ICES* ICEX† (μA) Max	h _{FE} Min	h _{FE} Max	IC (A) @ VCE & V _{CE} (V)	V _{CE} (SAT) (V) Max	V _{BE} (SAT) (V) Min	IC (A) @ V _{BE} (SAT) (V) Max	C _{ob} (pF) Max	f _T (MHz) Min	f _T (MHz) Max	IC (A) @	Process No.
D43C4	TO-202 (56)		45		1 μA	10	25	1A 200	0.5	1.3	1A	30				5P
D43C5	TO-202 (56)		45		1 μA	20	40	1A 200	0.5	1.3	1A	30				5P
D43C6	TO-202 (56)		45		1 μA	20	40	2A 200	0.5	1.3	1A	30				5P
D45C1	TO-220		30		10*	10	25	1 0.2	0.5	1.3	1	125	3	3	0.02	5P
D45C2	TO-220		30		10*	20	40	1 0.2	0.5	1.3	1	125	3	3	0.02	5P
D45C3	TO-220		30		10*	20	40	2 0.2	0.5	1.3	1	125	3	3	0.02	5P
D45C4	TO-220		45		10*	10	25	1 0.2	0.5	1.3	1	125	3	3	0.02	5P
D45C5	TO-220		45		10*	20	40	1 0.2	0.5	1.3	1	125	3	3	0.02	5P
D45C6	TO-220		45		10*	20	40	2 0.2	0.5	1.3	1	125	3	3	0.02	5P
D45C7	TO-220		60		10*	10	25	1 0.2	0.5	1.3	1	125	3	3	0.02	5P
D45C8	TO-220		60		10*	20	40	1 0.2	0.5	1.3	1	125	3	3	0.02	5P
D45C9	TO-220		60		10*	20	40	2 0.2	0.5	1.3	1	125	3	3	0.02	5P
D45C10	TO-220		80		10*	10	20	1 1	0.5	1.3	1	125	3	3	0.02	5P
D45C11	TO-220		80		10*	20	40	1 1	0.5	1.3	1	125	3	3	0.02	5P
D45C12	TO-220		80		10*	20	40	2 0.2	0.5	1.3	1	125	3	3	0.02	5P
MJE230	TO-126		40			40	20	0.2 2	0.3	1.8	0.5 2	70	50	50	0.1	5P
MJE231	TO-126		40			40	20	0.2 2	0.3	1.8	0.5 2	70	50	50	0.1	5P
MJE232	TO-126		40			25	10	0.2 1	0.3	1.8	0.5 2	70	50	50	0.1	5P
MJE233	TO-126		60			40	20	0.2 2	0.3	1.8	0.5 2	70	50	50	0.1	5P

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